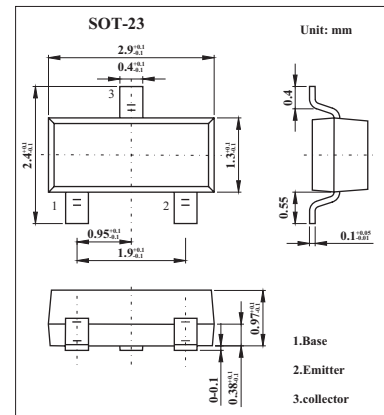


## Small Signal Transistor

## FMMT5089

## ■ Features

- Small signal transistor.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	30	V
Collector-emitter voltage	$V_{CEO}$	25	V
Emitter-base voltage	$V_{EBO}$	4.5	V
Collector current	$I_C$	50	mA
Power dissipation	$P_{tot}$	330	mW
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1\text{mA}, I_B=0$	30			V
Collector-emitter breakdown voltage *	$V_{(BR)CEO}$	$I_C=100\text{mA}, I_E=0^*$	25			V
Collector-base cut-off current	$I_{CBO}$	$V_{CB}=15\text{V}, I_E=0$			50	nA
Emitter-base current	$I_{EBO}$	$V_{EB(off)}=4.5\text{V}, I_C=0$			100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.8	V
DC current gain	$h_{FE}$	$I_C=100\mu\text{A}, V_{CE}=5\text{V}$	400		1200	
Current-gain-bandwidth product	$f_T$	$I_C=500\text{mA}, V_{CE}=5\text{V}, f=20\text{MHz}$	50			MHz
Output capacitance	$C_{obo}$	$V_{CB}=5\text{V}, f=1\text{MHz}, I_E=0$			4	pF
Emitter-base capacitance	$C_{ebo}$	$V_{BE}=0.5\text{V}, f=1\text{MHz}, I_C=0$			10	pF
Noise figure	NF	$I_C=200\text{mA}, V_{CE}=5\text{V}, R_g=10\text{K}\Omega, f=10\text{Hz to } 15\text{KHz}$			2	dB
Small signal current transfer ratio	$h_{fe}$	$I_C=1\text{mA}, V_{CE}=5\text{V}, f=1\text{KHz}$	450		1800	

\* Pulse test:  $t_p \leq 300 \mu\text{s}; d \leq 0.02$ .

## ■ Marking

Marking	1R